

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A structure comprising:
a buried cavity in a semiconductor material body having a shape, in cross section, in which a top wall, including a lattice having a first and a second layer, is approximately parallel with a horizontal plane of the semiconductor material body, side walls slope inward from the top wall to a bottom wall, and the bottom wall is approximately parallel with the top wall, and wherein said lattice has a plurality of interstitial openings filled with polycrystalline silicon.
2. (Previously Presented) The structure according to claim 1, wherein said first layer comprises silicon-dioxide, and said second layer comprises silicon-nitride.
- 3-5. (Canceled)
6. (Currently Amended) The structure according to claim ~~5~~1, wherein said top wall of said buried cavity further comprises a grown layer, and wherein communication openings extend through said ~~epitaxial-grown~~ layer and said lattice layer to said buried cavity.
7. (Currently Amended) The structure according to claim ~~3~~1, wherein each of said plurality of interstitial openings has a square shape, as viewed from above the horizontal plane of the semiconductor material body.
8. (Currently Amended) The structure according to claim ~~3~~1, wherein each of said plurality of interstitial openings has a rectangular shape, as viewed from above the horizontal plane of the semiconductor material body.

9. (Previously Presented) The structure according to claim 1, wherein said lattice is oriented to an angle of between 44° and 46° with respect to a flat of said semiconductor material body.

10. (Previously Presented) The structure according to claim 1, wherein said lattice is oriented to an angle of between 30° and 60° with respect to a particular crystallographic plane of said semiconductor material body.

11. (Canceled)

12. (Previously Presented) The structure of claim 13 wherein the cover further comprises a lattice layer formed on the upper surface of the body.

13. (Previously Presented) A structure, comprising:
a semiconductor material body;
a cavity formed within the body, the cavity having a substantially planar lower surface lying in a plane that is approximately parallel to a plane of an upper surface of the body;
a cover over the cavity comprising a polycrystalline-silicon coating layer formed on the upper surface of the body; and
a communication opening extending in the cover as far as the cavity.

14. (Original) The structure of claim 13, further comprising a layer grown on the polycrystalline-silicon layer.

15. (Canceled)

16. (Original) ~~The structure of claim 15 wherein the coating layer is a~~ A structure, comprising:

a semiconductor material body;

a cavity formed within the body;

a cover over the cavity comprising a lattice layer having a plurality of openings, formed on an upper surface of the body, and a polycrystalline-silicon coating layer formed on the lattice layer, the coating layer closing the plurality of openings; and
a communication opening extending through the coating layer in the cover as far as the cavity.

17. (Original) The structure of claim 16, further comprising a layer grown on the polycrystalline-silicon layer.